

SHEET 1 OF 1

<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449	<b>CUSTOMER NUMBER</b>  45114	ATTORNEY'S DKT No. H1102C	APPLICATION No. 10/720,166	
		APPLICANT(S) Shibly S. Ahmed et al.		
		FILING DATE November 25, 2003	GROUP 2822	

U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
MW	2005/0104091	05/2005	Tabery et al.	257	213	

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	

EXAMINER  MW, Iczewski	DATE CONSIDERED  10/2005
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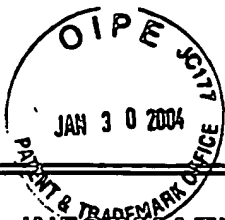
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<b>INFORMATION DISCLOSURE CITATION</b> PTO-1449		<b>CUSTOMER NUMBER</b>  26615		ATTORNEY'S DKT No. H1102C		APPLICATION No. 10/720,166	
				APPLICANT(S) Shibly S. AHMED et al.			
				FILING DATE November 25, 2003		GROUP <del>Unassigned</del> 2822	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
<i>MW</i>	6,583,469 B1	06/24/2003	Fried et al.	257	329		
<i>MW</i>	6,525,403 B2	02/25/2003	Inaba et al.	257	618		
<i>MW</i>	6,551,885 B1	04/22/2003	Yu	438	300		
<i>MW</i>	5,960,270	09/28/1999	Misra et al.	438	197		
<i>MW</i>	6,515,320 B1	02/04/2003	Azuma et al.	257	288		
<i>MW</i>	6,303,447 B1	10/16/2001	Chhagan et al.	438	299		
<i>MW</i>	6,342,410 B1	01/29/2002	Yu	438	164		
<i>MW</i>	6,265,256 B1	07/24/2001	An et al.	438	201		
<i>MW</i>	6,413,802 B1	07/02/2002	Hu et al.	438	151		
<i>MW</i>	6,406,951 B1	06/18/2002	Yu	438	183		
<i>MW</i>	6,551,886 B1	04/22/2003	Yu	438	300		
<i>MW</i>	6,475,890 B1	11/05/2002	Yu	438	574		
<i>MW</i>	6,562,665 B1	05/13/2003	Yu	438	149		
<i>MW</i>	6,458,662 B1	10/01/2002	Yu	438	286		
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation Yes No	
<i>MW</i>	WO 03/015182 A2	02/20/2003	WO			Abstract Only	
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
<i>MW</i>	United States Patent Application Publication No. US 2003/0111686 A1; Publication Date: June 19, 2003; Nowak.						
<i>MW</i>	United States Patent Application Publication No. US 2003/0141525 A1; Publication Date: July 31, 2003; Nowak						
<i>MW</i>	United States Patent Application Publication No. US 2003/0113970 A1; Publication Date: June 19, 2003; Fried et al.						
<i>MW</i>	United States Patent Application Publication No. US 2003/0151077 A1; Publication Date: August 14, 2003; Mathew et al.						
EXAMINER <i>MW</i> <i>Wlezewski</i>				DATE CONSIDERED <i>10/2005</i>			

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				APPLICANT(S) Shibly S. AHMED et al.			
				FILING DATE November 25, 2003		GROUP Unassigned <i>2802</i>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
<i>MW</i>	Copy of co-pending Application Serial No. 10/645,577; entitled "Sacrificial Oxide Protection During Dummy Gate Removal in Damascene Gate Process in Semiconductor Devices; filed on August 22, 2003; 28 pages.						
<i>MW</i>	Copy of co-pending Application Serial No. 10/320,536; entitled "FinFET Gate Formation Using Reverse Trim of Dummy Gate"; filed on December 17, 2002; 25 pages.						
<i>MW</i>	Copy of co-pending Application Serial No. 10/459,589; entitled "FinFET Gate Formation Using Reverse Trim and Oxide Polish"; filed on June 12, 2003; 45 pages.						
<i>MW</i>	Digh Hisamoto et al., "FinFET-A Self-Aligned Double-Gate MOSFET Scalable to 20 nm," IEEE Transactions on Electron Devices, Vol. 47, No. 12, December 2000, pages 2320-2325.						
<i>MW</i>	Yang-Kyu Choi et al., "Sub-20nm CMOS FinFET Technologies," 2001 IEEE, IEDM, pages 421-424.						
<i>MW</i>	Xuejue Huang et al., "Sub-50 nm P-Channel FinFET," IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pages 880-886.						
<i>MW</i>	Xuejue Huang et al., "Sub 50-nm FinFET: PMOS," 1999 IEEE, IEDM, pages 67-70.						
<i>MW</i>	Yang-Kyu Choi et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era," IEEE Electron Device Letters, Vol. 23, No. 1, January 2002, pages 25-27.						
EXAMINER <i>MW. Iczewski</i>				DATE CONSIDERED <i>10/2005</i>			

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			APPLICANT(S) Shibly S. AHMED et al.				
			FILING DATE November 25, 2003		GROUP Unassigned <i>2872</i>		
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
<i>MW</i>	Copy of U.S. Serial No. 10/754,559; filed January 12, 2004; entitled: "DAMASCENE TRI-GATE FINFET"; 28 pages.						
EXAMINER <i>MWileczewski</i>				DATE CONSIDERED <i>10/2005</i>			

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<div style="border: 1px solid black; border-radius: 50%; padding: 10px; display: inline-block; transform: rotate(-45deg);">             COPY              NO 26 2004              2/15/04           </div> <b>INFORMATION DISCLOSURE CITATION</b> PTO-1449		<b>CUSTOMER NUMBER</b>  26615	<b>ATTORNEY'S DKT No.</b> H1102C	<b>APPLICATION No.</b> 10/720,166			
			<b>APPLICANT(S)</b> Shibly S. Ahmed et al.				
			<b>FILING DATE</b> November 25, 2003	<b>GROUP</b> <del>4756</del> 2822			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
MW	6,396,108	05/28/02	Krivokapic et al.	257	365		
MW	5,801,397	09/01/98	Cunningham	257	66		
MW	6,686,231	02/03/04	Ahmed et al.	438	164		
<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
MW	Stephen H. Tang et al., "Comparison of Short-Channel Effect and Offstate Leakage in Symmetric vs. Asymmetric Double Gate MOSFETs", IEEE International SOI Conference, October 2000, pp. 120-121						
MW	United States Patent Application Publication No. US2002/0153587; publication date October 24, 2002; Adkisson et al.						
<b>EXAMINER</b>				<b>DATE CONSIDERED</b>			
MW Hczeuski				10/2005			

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		APPLICANT(s) Shibly S. Ahmed et al.	
		FILING DATE November 25, 2003	GROUP 1756 <i>2822</i>

**U.S. PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>MW</i>	6,645,797 B1	11/2003	Buynoski et al.	438	157	

**FOREIGN PATENT DOCUMENTS**

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**


EXAMINER <i>MWileczewski</i>	DATE CONSIDERED <i>10/2005</i>
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			APPLICANT(S) Shibly S. Ahmed et al.			
			FILING DATE November 25, 2003		GROUP 1756-2822	

U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
MW	6,764,884B1	07/20/2004	Yu et al.	438	157	
MW	6,465,823B1	10/15/2002	Yagishita et al.	438	157	
MW	6,765,303B1	07/20/04	Krivokapic et al.	257	903	
MW	6,509,611B1	01/21/03	Park et al.	257	330	
MW	2002/0177263A1	11/28/02	Hanafi et al.	438	183	
MW	2002/0153587A1	10/24/02	Adkisson et al.	257	510	

FOREIGN PATENT DOCUMENTS							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
MW	EP 1 383 164 A1	01/21/04	Europe				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)	

EXAMINER MW/czewski	DATE CONSIDERED 10/2005
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